further description can be found in original claims 2 and 3 and in the specification, from page 13, line 19 to page 15, line 15.

The grounds for claim 25-30 can be found in the specification, page 12, from line 14 to line 21, page 13 from line 19 to line 37, page 16, line 27, page 16, from line 33 to page18, page 19 line 23, and page 19, line 29 respectively.

Therefore, all grounds of rejection made for claims 1-11 and 15-22 are now believed to be met and are traversed.

The Examiner has found that none of the recited prior arts, i.e. Urano et al. teaches or suggests the present polysilazane of formula (II) of claim 3 and thus claim 3 would be allowable if rewritten in independent form including all of the limitations of the base claim 1. Furthermore, the Examiner has also found that Urano et al. does not teach or suggest the presently claimed photoacid generator, peroxide of claim 6.

It is to be noted that newly added claim 23 incorporates the novel polysilazane of formula (II) and photoacid generator, peroxide as a part of its limitation. Thus, claim 23 includes novel and useful steps that Urano et al does not teach. Wrong. Furthermore, Urano et al teaches a method of preparing a lithographic plate or a photoresist comprising a step in which a coated film is formed of a photosensitive composition comprising a polysilazane, which is different from the present formula (II), and a photoacid generator, a step in which the coated film is exposed to light in a pattern a step in which the exposed portion of the film is dissolved off so as to produce a patterned film. The resultant patterned polysilazane film is used as it is for a lithographic plate or a photo-resist. However, Urano et al, is silent about a method of making a patterned insulating film of the current invention which prepare such by further allowing the patterned polysilazane film to stand in an ambient atmosphere or baking the same to convert it to silica-based ceramic coating. Thus, Urano et al would not teach or suggest one of ordinarily skill in the art the current invention as claimed in claim 23 and its dependent claims 24-29.

Accordingly, consideration and allowance of claims 23-29 is respectfully requested.

Please deduct any necessary fees in connection with this matter from Deposit Account No. 01-1944.

Respectfully submitted,

Richard Klar
Registration No. 31,385

ANDERSON, KILL & OLICK
1251 Avenue of the Americas
New York, New York 10020-1182
(212) 278-1000

MAILING CERTIFICATE

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as first class mail in an envelope addressed: Commissioner of Patents & Trademarks, Washington, DC 20231 on Monday, January 6, 2003.

Jan. 6, 2003
Date

Maggie McGarry

Amended New Claims

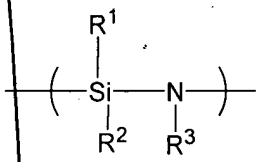
1-22. (cancelled)

23. (New) A method of forming a patterned insulating film comprising: a step in which a coated film is formed of a photosensitive polysilazane composition comprising a polysilazane and a photoacid generator, a step in which said coated film is exposed to light in a pattern, a step in which the exposed portion of said coated film is dissolved off, and a step in which the patterned polysilazane film formed as a result of said dissolving off is allowed to stand in an ambient atmosphere or baked to convert it to a silica-based ceramic coating, wherein said polysilazane is

a polysilazane having a number-average molecular weight of between 100 to 50,000, that mainly contains the skeleton represented with the following general formula, or a modification product thereof containing such polysilazane, or

a polysilazane having a number-average molecular weight of between 100 to 100,000, that mainly contains the skeleton represented with the following general formula (II), and wherein

said photoacid generator is at least one type of compound selected from the group consisting of a peroxide, a naphthoquinone diazidosulfonate ester and a nitrobenzyl ester:



general formula (I):

wherein, R^1, R^2 and R^3 respectively and independently represent a hydrogen atom, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, a group other than these groups in which the portion bonded directly to silicon or nitrogen is carbon, an alkylsilyl group, an alkylamino group or an alkoxy group;

general formula (II):

$$—(SiR^4(NR^5)_{1.5})_n—$$ (II)

wherein, R^4 and R^5respectively and independently represent a hydrogen atom, an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, a group other than these groups in which the portion bonded directly to silicon or nitrogen is carbon, an alkylsilyl group, an alkylamino group or an alkoxy group, and n is an arbitrary integer.

24. (New) A method of forming a patterned insulating film according to claim 24, wherein said polysilazane is a polyorganosiloxazane having a number-average molecular weight of between 300 to 100,000 that contains, as its main repeating unit, $-(RSiN_3)-$, $-(RSiN_2O)-$, $-(RSiNO_2)-$ and $-(RSiO_3)-$ in which R is an alkyl group, an alkenyl group, a cycloalkyl group, an aryl group, and alkylamino group or an alkylsilyl group.

25. (New) A method of forming a patterned insulating film according to claim 1, wherein said peroxide is t-butyl peroxybenzoate, 3,3`,4,4`-tetra(t-butylperoxycarbonyl) benzophenone or α,α`-bis(t-butylperoxy)diisopropylbenzene.

26. (New) A method of forming a patterned insulating film according to claim 24, wherein said photoacid generator further contains an sensitizing dye.

27. (New) A method of forming a patterned insulating film according to claim 27, wherein said sensitizing dye is selected from coumarin, ketocourmarin and their derivatives and thiopyrylium salts.

28. (New) A method of forming a patterned insulating film according to claim 24, wherein said photosensitive polysilazane composition further contains an oxidation catalyst.

29. (New) A method of forming a patterned insulating film according to claim 29, wherein said oxidation catalyst is palladium propionate.